

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	0	(method and forming and integrated and circuit and device and comprising and lower and electrode and substrate and dielectric and layer and upper and wherein and least and one and comprises and ruthenium and film and having and stratified and oxygen and concentration and profile).clm.	US-PGPUB	OR	ON	2007/04/15 21:40